

L Number	Hits	Search Text	DB	Time stamp
2	104098	((detach\$3 remov\$3) near10 (wafer substrate)	USPAT; US-PGPUB	2003/11/14 18:04
3	57609	((detach\$3 remov\$3) near10 (wafer substrate)) and (insulat\$3 dielectric)	US-PGPUB	2003/11/14 18:04
4	50728	((detach\$3 remov\$3) near10 (wafer substrate)) and (insulat\$3 dielectric)) and (etch\$3 pattern\$3)	USPAT; US-PGPUB	2003/11/14 18:05
5	47194	((((detach\$3 remov\$3) near10 (wafer substrate)) and (insulat\$3 dielectric)) and (etch\$3 pattern\$3)) and (metal contact wire)	USPAT; US-PGPUB	2003/11/14 20:37
7	3843	(((((detach\$3 remov\$3) near10 (wafer substrate)) and (insulat\$3 dielectric)) and (etch\$3 pattern\$3)) and (metal contact wire)) and Sacrificial	USPAT; US-PGPUB	2003/11/14 20:39
8	915	(((((detach\$3 remov\$3) near10 (wafer substrate)) and (insulat\$3 dielectric)) and (etch\$3 pattern\$3)) and (metal contact wire)) and Sacrificial	USPAT; US-PGPUB	2003/11/14 21:18
9	153115	438/\$.cc1s. or 257/\$.cc1s.	USPAT; US-PGPUB	2003/11/14 21:20
10	40539	((detach\$3 remov\$3) near10 (wafer substrate)) and (438/\$.cc1s. or 257/\$.cc1s.)	USPAT; US-PGPUB	2003/11/14 21:20
11	28706	((detach\$3 remov\$3) near10 (wafer substrate)) and (438/\$.cc1s. or 257/\$.cc1s.) and (((detach\$3 remov\$3) near10 (wafer substrate)) and (insulat\$3 dielectric)) and (etch\$3 pattern\$3)) and (metal contact wire))	USPAT; US-PGPUB	2003/11/14 21:21
12	2654	(((((detach\$3 remov\$3) near10 (wafer substrate)) and (438/\$.cc1s. or 257/\$.cc1s.)) and (((detach\$3 remov\$3) near10 (wafer substrate)) and (insulat\$3 dielectric)) and (etch\$3 pattern\$3)) and (metal contact wire))) and (((detach\$3 remov\$3) near10 (wafer substrate)) and (insulat\$3 dielectric)) and (etch\$3 pattern\$3)) and (metal contact wire)) and Sacrificial	USPAT; US-PGPUB	2003/11/14 21:23